

LMP91050 Configurable AFE for Nondispersive Infrared (NDIR) Sensing Applications

Check for Samples: LMP91050

FEATURES

- Programmable Gain Amplifier
- "Dark Signal" Offset Cancellation
- Supports External Filtering
- Common Mode Generator and 8 bit DAC

APPLICATIONS

- NDIR Sensing
- Demand Control Ventilation
- Building Monitoring
- CO2 Cabin Control Automotive
- Alcohol Detection Automotive
- Industrial Safety and Security
- GHG & Freons Detection Platforms

KEY SPECIFICATIONS

- Programmable gain 167 to 7986 V/V
- Low noise (0.1 to 10 Hz) 0.1 µVRMS
- Gain Drift 100 ppm/°C (max)
- Phase Delay Drift 500 ns (max)
- Power supply voltage range 2.7 to 5.5 V

DESCRIPTION

The LMP91050 is a programmable integrated Sensor Analog Front End (AFE) optimized for thermopile sensors, as typically used in NDIR applications. It provides a complete signal path solution between a sensor and microcontroller that generates an output voltage proportional to the thermopile voltage. The LMP91050's programmability enables it to support multiple thermopile sensors with a single design as opposed to the multiple discrete solutions.

The LMP91050 features a programmable gain amplifier (PGA), "dark phase" offset cancellation, and an adjustable common mode generator (1.15V or 2.59V) which increases output dynamic range. The PGA offers a low gain range of 167V/V to 1335V/V plus a high gain range of 1002V/V to 7986V/V which enables the user to utilize thermopiles with different sensitivities. The PGA is highlighted by low gain drift (100 ppm/°C), output offset drift (1.2mV/°C at G = 1002 V/V), phase delay drift (500ns) and noise specifications (0.1 μV_{RMS} 0.1 to 10Hz) . The offset cancellation circuitry compensates for the "dark signal" by adding an equal and opposite offset to the input of the second stage, thus removing the original offset from the output signal. This offset cancellation circuitry allows optimized usage of the ADC full scale and relaxes ADC resolution requirements.

The LMP91050 allows extra signal filtering (high pass, low pass or band pass) through dedicated pins A0 and A1, in order to remove out of band noise. The user can program through the on board SPI interface. Available in a small form factor 10–pin package, the LMP91050 operates from -40 to +105°C.

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Block Diagram

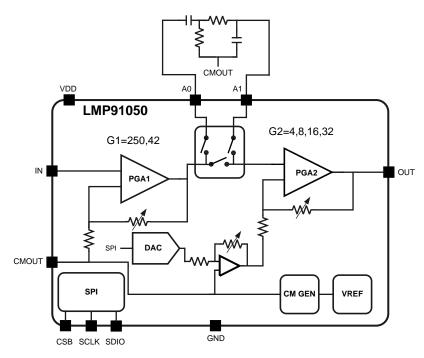


Figure 1. Configurable AFE for NDIR

Typical Application

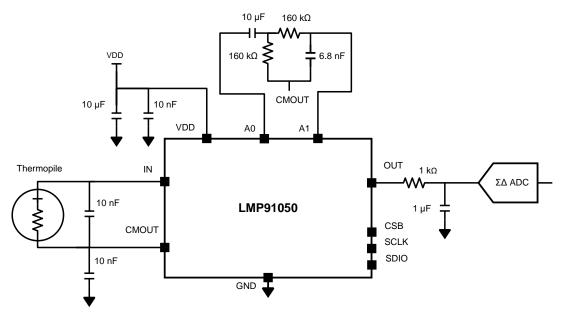
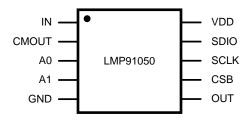


Figure 2. Typical NDIR Sensing Application Circuit

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Connection Diagram



Pin Descriptions

Pin	Symbol	Туре	Description	
1	N	Analog Input	Signal Input	
2	CMOUT	Analog Output	Common Mode Voltage Output	
3	A0	Analog Output	First Stage Output	
4	A1	Analog Input	Second Stage Input	
5	GND	Power	Ground	
6	ОИТ	Analog Output Signal Output, reference to the same potential a CMOUT		
7	CSB	Digital Input	Chip Select, active low	
8	SCLK	Digital Input	Interface Clock	
9	SDIO	Digital Input / Output	t Serial Data Input / Output	
10	VDD	Power	Positive Supply	



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

ESD Tolerance ⁽³⁾	Human Body Model	2500V
	Machine Model	250V
	Charged Device Model	1250V
Supply Voltage (VDD)		-0.3V to 6.0V
Voltage at Any Pin		- 0.3V to VDD + 0.3V
Input Current at Any Pin	5mA	
Storage Temperature Range	-65°C to 150°C	
Junction Temperature ⁽⁴⁾		150°C
For soldering specifications: see product folder at www.ti.com and	http://www.ti.com/lit/SNOA549.	

^{(1) &}quot;Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Operating Ratings is not implied. Operating Ratings indicate conditions at which the device is functional and the device should not be operated beyond such conditions.

⁽²⁾ If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

⁽³⁾ Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field- Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

⁽⁴⁾ The maximum power dissipation is a function of T_{J(MAX)}, θ_{JA}, and the ambient temperature, TA. The maximum allowable power dissipation at any ambient temperature is P_{DMAX} = (T_{J(MAX)} - T_A)/θ_{JA} All numbers apply for packages soldered directly onto a PC board.



Operating Ratings (1)

Supply Voltage	2.7V to 5.5V
Junction Temperature Range	-40°C to 105°C
Package Thermal Resitance, θ_{JA} 10 Lead VSSOP	176 °C/W

- (1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Operating Ratings is not implied. Operating Ratings indicate conditions at which the device is functional and the device should not be operated beyond such conditions.
- (2) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and the ambient temperature, TA. The maximum allowable power dissipation at any ambient temperature is $P_{DMAX} = (T_{J(MAX)} T_A)/\theta_{JA}$ All numbers apply for packages soldered directly onto a PC board.

Electrical Characteristics(1)

The following specifications apply for VDD = 3.3V, VCM = 1.15V, **Bold** values for $T_A = -40^{\circ}\text{C}$ to +85°C unless otherwise specified. All other limits apply to $T_A = T_J = +25^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max (2)	Units
Power Sup	ply					
VDD	Supply Voltage		2.7	3.3	5.5	V
IDD	Supply Current	All analog block ON	3.1	3.7	4.2	mA
	Power Down Supply Current	All analog block OFF	45	85	121	μΑ
Offset Cand	cellation (Offset DAC)					
	Resolution			256		steps
	LSB	All gains		33.8		mV
	DNL		-1		2	LSB
	Error	Output referred offset error, all gains		±100		mV
	Offset adjust Range	Output referred, all gains	0.2		VDD - 0.2	V
	DAC settling time			480		μs
Programma	ble Gain Amplifier (PGA) 1st S	tage, R_L = 10kΩ, C_L = 15pF				
IBIAS	Bias Current			5	200	рА
VINMAX _HGM	Max input signal High gain mode	Referenced to CMOUT voltage, it refers to the maximum voltage at the IN pin before clipping; It		±2		mV
VINMAX _LGM	Max input signal Low gain mode	includes dark voltage of the thermopile and signal voltage.		±12		mV
VOS	Input Offset Voltage			-165		μV
G _HGM	Gain High gain mode			250		V/V
G_LGM	Gain Low gain mode			42		V/V
GE	Gain Error	Both HGM and LGM		2.5		%
VOUT	Output Voltage Range		0.5		VDD - 0.5	V
PhDly	Phase Delay	1mV input step signal, HGM, Vout measured at Vdd/2		6		μs
TCPhDly	Phase Delay variation with Temperature	1mV input step signal, HGM, Vout measured at Vdd/2,		416		ns
SSBW	Small Signal Bandwidth	Vin = 1mVpp, Gain = 250 V/V		18		kHz
Cin	Input Capacitance			100		pF

⁽¹⁾ Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T_J = T_A. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.

⁽²⁾ Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.

⁽³⁾ Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.



Electrical Characteristics(1) (continued)

The following specifications apply for VDD = 3.3V, VCM = 1.15V, **Bold** values for $T_A = -40$ °C to +85°C unless otherwise specified. All other limits apply to $T_A = T_J = +25$ °C.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max (2)	Units
Programma	ble Gain Amplifier (PGA) 2nd St	age, $R_S = 1$ kΩ, $C_L = 1$ μF				
VINMAX	Max input signal	GAIN = 4 V/V		1.65		V
VINMIN	Min input signal			0.82		V
G	Gain	Programmable in 4 steps	4		32	V/V
GE	Gain Error	Any gain		2.5		%
VOUT	Output Voltage Range		0.2		VDD - 0.2	V
PhDly	Phase Delay	100mV input sine 35kHz signal, Gain = 8, VOUT measured at 1.65V, $R_L = 10k\Omega$		1		μs
TCPhDly	Phase Delay variation with Temperature	250mV input step signal, Gain = 8, Vout measured at Vdd/2		84		ns
SSBW	Small Signal Bandwidth	Gain = 32 V/V		360		kHz
Cin	Input Capacitance			5		pF
CLOAD, OUT	OUT Pin Load Capacitance	Series RC		1		μF
RLOAD, OUT	OUT Pin Load Resistance	Series RC		1		kΩ
Combined A	Amplifier Chain Specification			I		
en	Input-Referred Noise Density	Combination of both current and voltage noise, with a $86k\Omega$ source impedance at 5Hz, Gain = 7986		30		nV/√ Hz
	Input-Referred Integrated Noise	Combination of both current and voltage noise, with a $86k\Omega$ source impedance 0.1Hz to 10Hz, Gain = 7986		0.1	0.12	μVrms
		PGA1 GAIN = 42, PGA2 GAIN = 4		167		
		PGA1 GAIN = 42, PGA2 GAIN = 8		335		
		PGA1 GAIN = 42, PGA2 GAIN = 16		669		
0	Osis	PGA1 GAIN = 42, PGA2 GAIN = 32		1335		
G	Gain	PGA1 GAIN = 250, PGA2 GAIN = 4		1002		V/V
		PGA1 GAIN = 250, PGA2 GAIN = 8		2004		
		PGA1 GAIN = 250, PGA2 GAIN = 16		4003		
		PGA1 GAIN = 250, PGA2 GAIN = 32		7986		
GE	Gain Error	Any gain		5		%
TCCGE	Gain Temp Coefficient (5)				100	ppm/°C
PSRR	Power Supply Rejection Ratio	DC, 3.0V to 3.6V supply, gain = 1002V/V	90	110		dB
PhDly	Phase Delay	1mV input step signal, Gain = 1002, Vout measured at Vdd/2		9		μs
TCPhDly	Phase Delay variation with Temperature ⁽⁶⁾	1mV input step signal, Gain=1002, Vout measured at Vdd/2			500	ns

Specified by design and characterization. Not tested on shipped production material.

TCCGE and TCVOS are calculated by taking the largest slope between -40°C and 25°C linear interpolation and 25°C and 85°C linear

TCPhDly is largest change in phase delay between -40°C and 25°C measurements and 25°C and 85°C measurements.



Electrical Characteristics⁽¹⁾ (continued)

The following specifications apply for VDD = 3.3V, VCM = 1.15V, **Bold** values for T_A = -40°C to +85°C unless otherwise specified. All other limits apply to T_A = T_J = +25°C.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max (2)	Units
		Gain = 167 V/V	-0.525		0.525	
		Gain = 335 V/V	-0.60		0.60	
		Gain = 669 V/V	-0.90		0.90	
TCVOS	Output Offset Voltage	Gain = 1335 V/V	-1.50		1.50	mV/°C
1000	Output Offset Voltage Temperature Drift ⁽⁵⁾	Gain = 1002 V/V	-1.20		1.20	mv/°C
		Gain = 2004 V/V	-1.90		1.90	
		Gain = 4003 V/V	-3.70		3.70	
		Gain = 7986V/V	-7.10		7.10	
Common M	lode Generator					
VCM	Common Mode Voltage	Programmable, see Common Mode Generation		1.15 or 2.59		V
	VCM accuracy			2		%
CLOAD	CMOut Load Capacitance			10		nF

SPI Interface⁽¹⁾

The following specifications apply for VDD = 3.3V, VCM = 1.15V, $C_L = 15pF$, **Bold** values for $T_A = -40^{\circ}C$ to +85°C unless otherwise specified. All other limits apply to $T_A = T_{,l} = +25^{\circ}C$.

Symbol	Parameter	Conditions	Min (2)	Тур (3)	Max (2)	Units
V _{IH}	Logic Input High		0.7 × VDD			٧
V _{IL}	Logic Input Low				0.8	V
V _{OH}	Logic Output High		2.6			V
V _{OL}	Logic Output Low				0.4	V
IIH/IIL	Input Digital Leakage Current		-100 -200		100 200	nA

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T_J = T_A. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.

Timing Characteristics (1)

The following specifications apply for VDD = 3.3V, VCM = 1.15V, C_L = 15pF, **Bold** values for T_A = -40°C to +85°C unless otherwise specified. All other limits apply to T_A = T_J = +25°C.

Symbol	Parameter	Conditions	Min (2)	Тур (3)	Max (2)	Units
t _{WU}	Wake up time			1		ms
f _{SCLK}	Serial Clock Frequency				10	MHz

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T_J = T_A. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.



Timing Characteristics (1) (continued)

The following specifications apply for VDD = 3.3V, VCM = 1.15V, C_L = 15pF, **Bold** values for T_A = -40°C to +85°C unless otherwise specified. All other limits apply to T_A = T_J = +25°C.

Symbol	Parameter	Conditions	Min (2)	Typ (3)	Max (2)	Units
t _{PH}	SCLK Pulse Width High		0.4/f _{SCLK}			ns
t _{PL}	SCLK Pulse Width Low		0.4/f _{SCLK}			ns
t _{CSS}	CSB Setup Time		10			ns
t _{CSH}	CSB Hold Time		10			ns
t _{SU}	SDI Setup Time prior to rise edge of SCLK		10			ns
t _{SH}	SDI Hold Time prior to rise edge of SCLK		10			ns
t _{DOD1}	SDO Disable Time after rise edge of CSB				45	ns
t _{DOD2}	SDO Disable Time after 16 th rise edge of SCLK				45	ns
t _{DOE}	SDO Enable Time from the fall edge of 8 th SCLK				35	ns
t _{DOA}	SDO Access Time after the fall edge of SCLK				35	ns
t _{DOH}	SDO hold time after the fall edge of SCLK		5			ns
t _{DOR}	SDO Rise time			5		ns
t _{DOF}	SDO Fall time			5		ns

Timing Diagrams

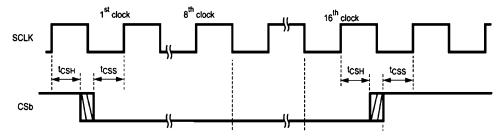


Figure 3. SPI Timing Diagram

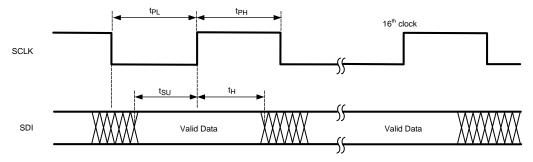


Figure 4. SPI Set-up Hold Time



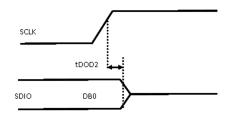


Figure 5. SDO disable time after 16th rise edge of SCLK

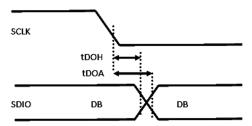


Figure 6. SDO access time (t_{DOA}) and SDO hold time (t_{DOH}) after the fall edge of SCLK

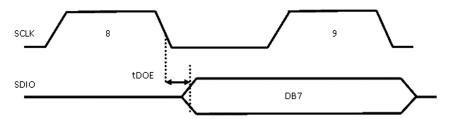


Figure 7. SDO Enable time from the fall edge of 8th SCLK

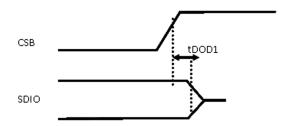


Figure 8. SDO disable time after rise edge of CSB

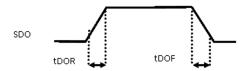


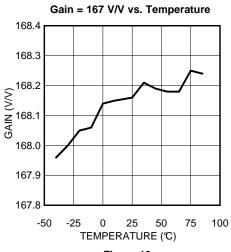
Figure 9. SDO rise and fall times

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Typical Performance Characteristics

VDD = +3.3V, VCM = 1.15V, and $T_A = 25$ °C unless otherwise noted





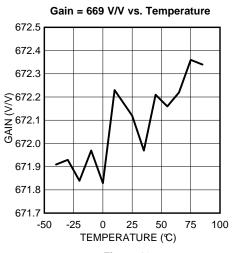
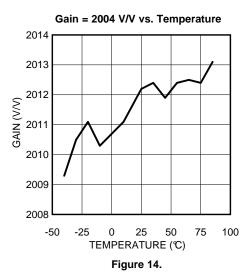


Figure 12.



Gain = 335 V/V vs. Temperature

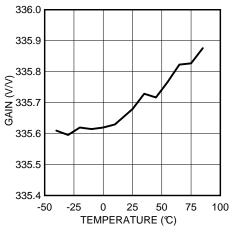
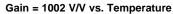


Figure 11.



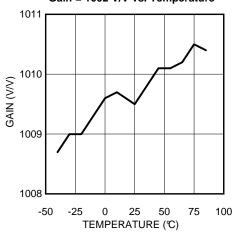


Figure 13.

Phase Delay vs. Temperature

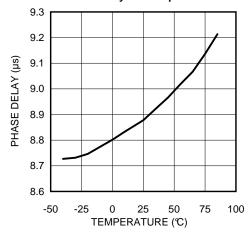


Figure 15.



Typical Performance Characteristics (continued)

VDD = +3.3V, VCM = 1.15V, and T_A = 25°C unless otherwise noted

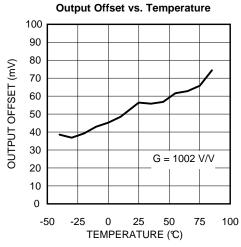
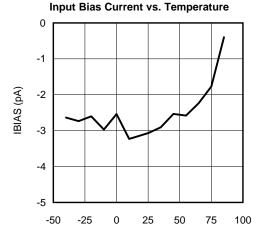
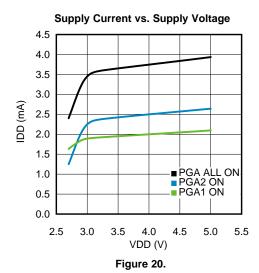


Figure 16.



TEMPERATURE (℃)

Figure 18.





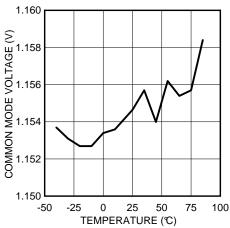
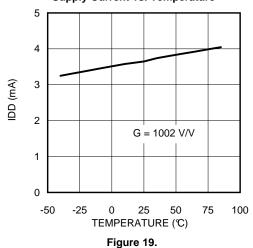


Figure 17.

Supply Current vs. Temperature



Power Down Supply Current vs. Supply Voltage

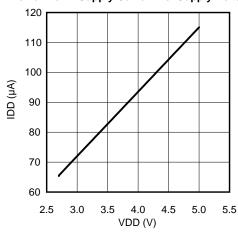


Figure 21.

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Typical Performance Characteristics (continued)

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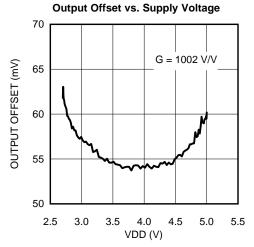
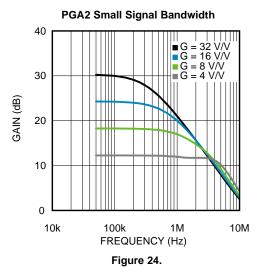


Figure 22.



Input-Referred Noise Density vs. Frequency 140 120 NOISE DENSITY (nV/√Hz) 100 80 60 40 20 0 100m 10 100 1k 10k FREQUENCY (Hz)

Figure 26.

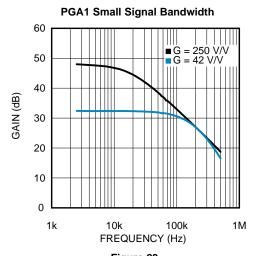


Figure 23.

Power Supply Rejection Ratio vs. Frequency

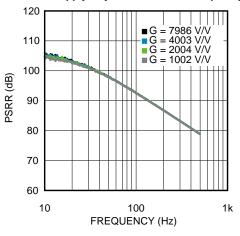


Figure 25.

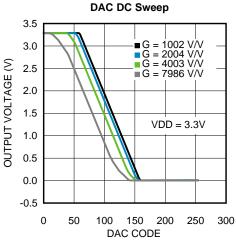


Figure 27.



Typical Performance Characteristics (continued)

VDD = +3.3V, VCM = 1.15V, and T_A = 25°C unless otherwise noted

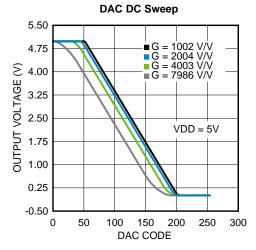


Figure 28.



FUNCTIONAL DESCRIPTION

PROGRAMMABLE GAIN AMPLIFIER

The LMP91050 offers two programmable gain modes (low/high) with four programmable gain settings each. The purpose of the gain mode is to enable thermopiles with larger dark voltage levels. All gain settings are accessible through bits GAIN1 and GAIN2[1:0]. The low gain mode has a range of 167 V/V to 1335 V/V while the high gain mode has a range of 1002 V/V to 7986 V/V. The PGA is referenced to the internally generated VCM. Input signal, referenced to this VCM voltage, should be within +/-2mV (see VINMAX_HGM specification) in high gain mode. In the low gain mode the first stage will provide a gain of 42 V/V instead of 250 V/V, thus allowing a larger maximum input signal up to +/-12mV (VINMAX_LGM).

Table 1. Gain Modes

Bit Symbol	Gain
CAINIA	0: 250 (default)
GAIN1	1: 42
	00: 4 (default)
CAING [4:0]	01: 8
GAIN2 [1:0]	10: 16
	11: 32

EXTERNAL FILTER

The LMP91050 offers two different measurement modes selectable through EXT_FILT bit. EXT_FILT bit is present in the Device configuration register and is programmable through SPI.

Table 2. Measurement Modes

Bit Symbol	Measurement Mode
EXT_FILT	0: The signal from the thermopile is being processed by the internal PGAs, without additional external decoupling or filtering (default).
	1: The signal from the thermopile is being processed by the first internal PGA and fed to the A0 pin. An external low pass, high pass or band pass filter can be connected through pins A0, A1.

An external filter can be applied when EXT_FILT = 1. A typical band pass filter is shown in the picture below. Resistor and capacitor can be connected to the CMOUT pin of the LMP91050 as shown. Discrete component values have been added for reference.

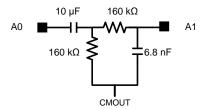


Figure 29. Typical Bandpass Filter

OFFSET ADJUST

Procedure of the offset adjust is to first measure the "dark signal", program the DAC to adjust, and then measure in a second cycle the residual of the dark signal for further signal manipulation within the μ C. The signal source is expected to have an offset component (dark signal) larger than the actual signal. During the "dark phase", the time when no light is detected by the sensor, the μ C can program LMP91050 internal DAC to compensate for a measured offset. A low output offset voltage temperature drift (TCVOS) ensures system accuracy over temperature. See Figure 30 below which plots the maximum TCVOS allowed over a given temperature drift in order to achieve n bit system accuracy.

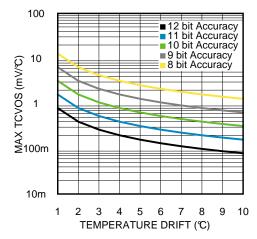


Figure 30. System Accuracy vs. TCVOS and Temperature Drift

COMMON MODE GENERATION

As the sensor's offset is bipolar, there is a need to supply a VCM to the sensor. This can be programmed as 1.15V or 2.59V (approximately mid rail of 3.3V or 5V supply). It is not recommended to use 2.59V VCM with 3.3V supply

SPI INTERFACE

An SPI interface is available in order to program the device parameters like PGA gain of two stages, enabling external filter, enabling power for PGAs, offset adjust and common mode (VCM) voltage.

Interface Pins

The Serial Interface consists of SDIO (Serial Data Input / Output), SCLK (Serial Interface Clock) and CSB (Chip Select Bar). The serial interface is write-only by default. Read operations are supported after unlocking the SDIO_MODE_PASSWD. This is discussed in detail later in the document.

CSB

Chip Select is a active-low signal. CSB needs to be asserted throughout a transaction. That is, CSB should not pulse between the Instruction Byte and the Data Byte of a single transaction.

Note that CSB de-assertion always terminates an on-going transaction, if it is not already complete. Likewise, CSB assertion will always bring the device into a state, ready for next transaction, regardless of the termination status of a previous transaction.

CSB may be permanently tied low for a 2-wire SPI communication protocol.

SCLK

SCLK can idle High or Low for a write transaction. However, for a READ transaction, SCLK should idle high. SCLK features a Schmitt-triggered input and although it has hysterisis, it is recommende to keep SCLK as clean as possible to prevent glitches from inadvertently spoiling the SPI frame.

Communication Protocol

Communication on the SPI normally involves Write and Read transactions. Write transaction consists of single Write Command Byte, followed by single Data byte. The following figure shows the SPI Interface Protocol for write transaction.



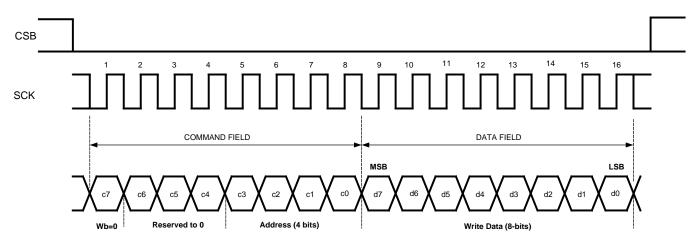
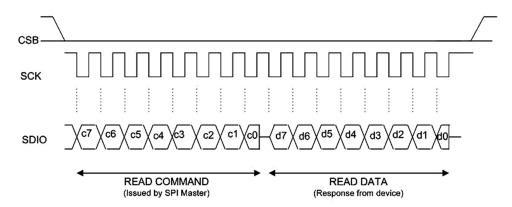


Figure 31. SPI Interface Protocol

For Read transactions, user first needs to write into a SDIO mode enable register for enabling the SPI read mode. Once the device is enabled for Reading, the data is driven out on the SDIO pin during the Data field of the Read Transaction. SDIO pin is designed as a bidirectional pin for this purpose. Figure 32 shows the Read transaction. The sequence of commands that need to be issued by the SPI Master to enable SPI read mode is illustrated in Figure 33.

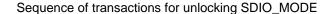
READ TRANSACTION

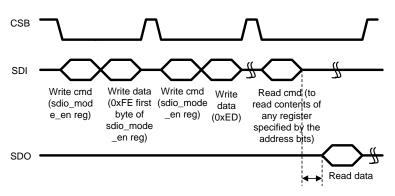


Note: Read command is issued by the SPI Master, who after issuing the c0 (LSBit of the command byte) bit should relinquish the data line (high-Z) after meeting the hold timing(10ns) and stop SCK idling high.

Figure 32. Read Transaction







Bus turnaround time = half cycle

Note:

- 1. Once the SDIO_mode is unlocked. The user can read as many registers as long as nothing else is written to sdio_mode_en register to disturb the state of SDIO_mode
- 2. The separate signals SDI and SDO are given in the figure for the sake of understanding. However, only one signal SDIO exists in the design

Figure 33. Enable SDIO Mode for reading SPI registers

Registers Organization

Configuring the device is achieved using 'Write' of the designated registers in the device. All the registers are organized into individually addressable byte-long registers that have a unique address. The format of the Write/Read instruction is as shown below.

Table 3. Write / Read Instruction Format

Bit[7]	Bit[6:4]	Bit[3:0]
0 : Write Instruction	Decemined to 0	Address
1 : Read Instruction	Reserved to 0	Address

REGISTERS

This section describes the programmable registers and the associated programming sequence, if any, for the device. The following table shows the summary listing of all the registers that are available to the user and their power-up values.

Title	Address (Hex)	Туре	Power-up/Reset Value (Hex)	
Davies Configuration	0.40	Read-Write	0x0	
Device Configuration	0x0	(Read allowed in SDIO Mode)		
DAC Configuration	0v4	Read-Write	0,400	
DAC Configuration	0x1	(Read allowed in SDIO Mode)	0x80	
SDIO Mode Enable 0xF		Write-only	0x0	

Device Configuration – Device Configuration Register (Address 0x0)

Bit	Bit Symbol	Description
7	RESERVED	Reserved to 0.



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Bit	Bit Symbol	Description	
		00: PGA1 OFF PGA2 OFF (default)	
[0.5]	- FN	01: PGA1 OFF, PGA2 ON	
[6:5]	EN	10: PGA1 ON, PGA2 OFF	
		11: PGA1 ON, PGA2 ON	
4	EXT FILT	0: PGA1 to PGA2 direct (default)	
4	EXI_FILI	1: PGA1 to PGA2 via external filter	
3	CMN MODE	0 : 1.15V (default)	
3	CMN_MODE	1:2.59V	
		00: 4 (default)	
[2:4]	GAIN2	01: 8	
[2:1]		10: 16	
		11: 32	
0	GAIN1	0: 250 (default)	
U	GAINT	1: 42	

DAC Configuration – DAC Configuration Register (Address 0x1)

The output DC level will shift according to the formula Vout_shift = -33.8mV * (NDAC - 128).

Bit	Bit Symbol	Description
[7:0]	NDAC	128 (0x80): Vout_shift = -33.8mV * (128 - 128) = 0mV (default)

SDIO Mode - SDIO Mode Enable Register (Address 0xf)

Write-only

Bit	Bit Symbol	Description
[7.0]	CDIO MODE EN	To enter SDIO Mode, write the successive sequence 0xFE and 0xED.
[7:0]	SDIO_MODE_EN	Write anything other than this sequence to get out of mode.

SNAS517D - NOVEMBER 2011 - REVISED MARCH 2013



REVISION HISTORY

Cł	nanges from Revision C (March 2013) to Revision D	Pa	ge
•	Changed layout of National Data Sheet to TI format		17

Submit Documentation Feedback



PACKAGE OPTION ADDENDUM

11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
LMP91050MM/NOPB	ACTIVE	VSSOP	DGS	10	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 105	AN8A	Samples
LMP91050MME/NOPB	ACTIVE	VSSOP	DGS	10	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 105	AN8A	Samples
LMP91050MMX/NOPB	ACTIVE	VSSOP	DGS	10	3500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 105	AN8A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Tl's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, Tl Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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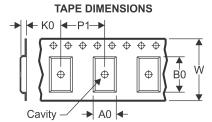
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PACKAGE MATERIALS INFORMATION

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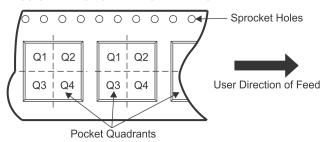
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

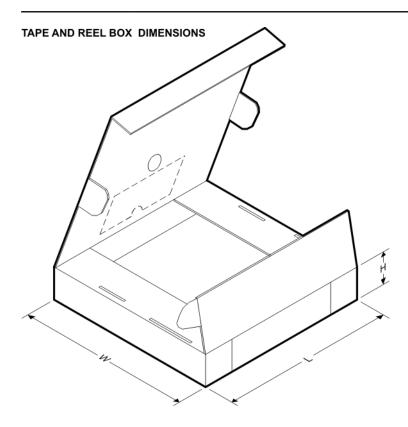
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMP91050MM/NOPB	VSSOP	DGS	10	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMP91050MME/NOPB	VSSOP	DGS	10	250	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMP91050MMX/NOPB	VSSOP	DGS	10	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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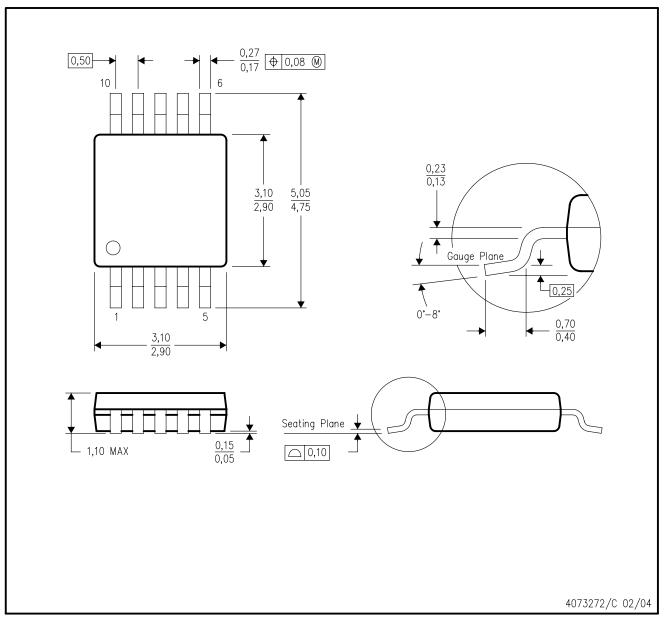


*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
LMP91050MM/NOPB	VSSOP	DGS	10	1000	210.0	185.0	35.0	
LMP91050MME/NOPB	VSSOP	DGS	10	250	210.0	185.0	35.0	
LMP91050MMX/NOPB	VSSOP	DGS	10	3500	367.0	367.0	35.0	

DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



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